

High Efficiency Thyristor

$$V_{\text{DRM}} = 1200 \text{ V}$$

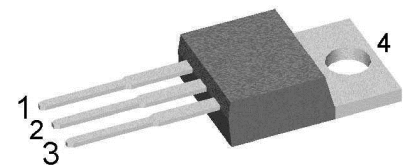
$$I_{\text{TAV}} = 20 \text{ A}$$

$$V_{\text{T}} = 1.4 \text{ V}$$

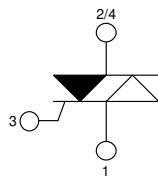
Triode
Single Reverse Conducting Thyristor

Part number

CLA20EF1200PB



Backside: anode



Features / Advantages:

- Thyristor for fast turn-on switching
- Integrated free wheeling diode
- Planar passivated chip
- Long-term stability

Applications:

- Ignition for HD lamps
- Capacity discharge

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

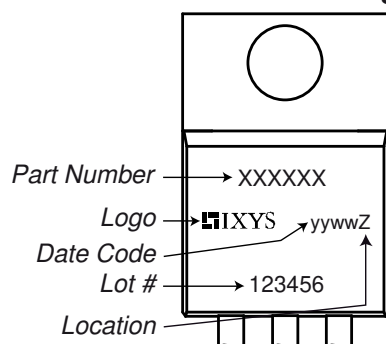
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Thyristor				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{DSM}	max. non-repetitive forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1300	V
V_{DRM}	max. repetitive forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
I_D	drain current	$V_D = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			10	μA
		$V_D = 1200\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$			1	mA
V_T	forward voltage drop Note: reverse voltage drop $\sim 1.2 \times V_T$	$I_T = 20\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.40	V
		$I_T = 40\text{ A}$				1.60	V
		$I_T = 20\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.40	V
		$I_T = 40\text{ A}$				1.60	V
I_{TAV}	average forward current	$T_C = 115^{\circ}\text{C}$ DC	$T_{VJ} = 150^{\circ}\text{C}$			20	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}\text{C}$			0.90	V
r_T	slope resistance					25	m Ω
R_{thJC}	thermal resistance junction to case					0.65	K/W
R_{thCH}	thermal resistance case to heatsink				0.5		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			190	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			120	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			130	A
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			100	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			110	A
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			72	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			70	A ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			50	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			50	A ² s
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		6		pF
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 150^{\circ}\text{C}$			10	W
		$t_p = 300\text{ }\mu\text{s}$				5	W
P_{GAV}	average gate power dissipation					0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 60\text{ A}$ $t_p = 1\text{ }\mu\text{s}; di_G/dt = 0.5\text{ A}/\mu\text{s}; I_{TSA} = 600\text{ A}$				500	A/ μs
		$I_G = 0.07\text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 20\text{ A}$				1500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}\text{C}$			500	V/ μs
		$R_{GK} = \infty$; method 1 (linear voltage rise)					
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1.3	V
			$T_{VJ} = -40^{\circ}\text{C}$			1.6	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			20	mA
			$T_{VJ} = -40^{\circ}\text{C}$			35	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}\text{C}$			0.2	V
I_{GD}	gate non-trigger current					1	mA
I_L	latching current	$t_p = 10\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$			30	mA
		$I_G = 0.07\text{ A}; di_G/dt = 0.5\text{ A}/\mu\text{s}$					
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$			25	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}\text{C}$			2	μs
		$I_G = 0.07\text{ A}; di_G/dt = 0.5\text{ A}/\mu\text{s}$					
t_q	turn-off time	$V_R = 0\text{ V}; I_T = 20\text{ A}; V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 125^{\circ}\text{C}$ $di/dt = 10\text{ A}/\mu\text{s}$ $dv/dt = 20\text{ V}/\mu\text{s}$ $t_p = 200\text{ }\mu\text{s}$			150		μs

Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			35	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				2		g
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N

Product Marking



Part description

C = Thyristor (SCR)
 L = High Efficiency Thyristor
 A = (up to 1200V)
 20 = Current Rating [A]
 EF = Single Reverse Conducting Thyristor
 1200 = Reverse Voltage [V]
 PB = TO-220AB (3)

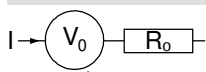
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CLA20EF1200PB	CLA20EF1200PB	Tube	50	516273

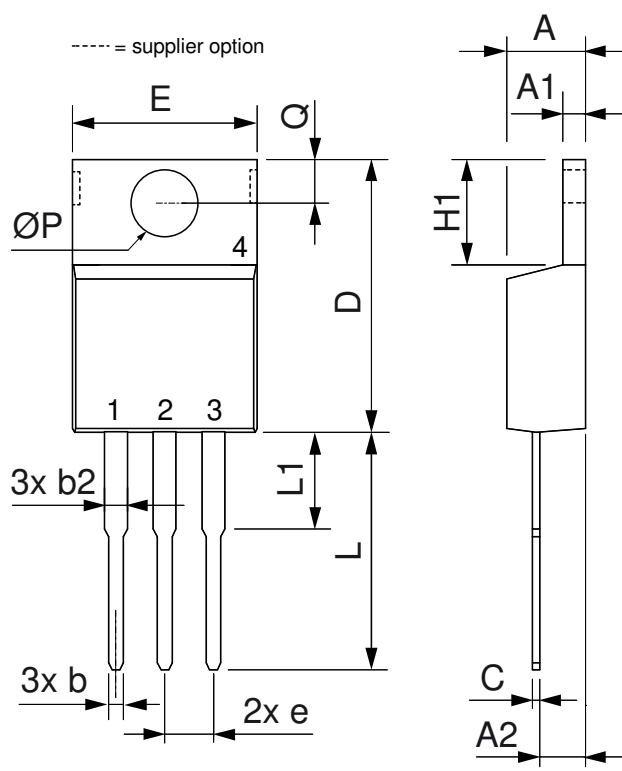
Similar Part	Package	Voltage class
CLA20EF1200PZ	TO-263AB (D2Pak) (2HV)	1200

Equivalent Circuits for Simulation

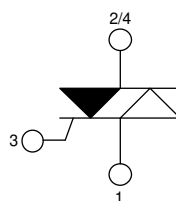
* on die level

 $T_{VJ} = 150^{\circ}\text{C}$

		Thyristor	
$V_{0\max}$	threshold voltage	0.9	V
$R_{0\max}$	slope resistance *	22	mΩ

Outlines TO-220


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	2.54	BSC	0.100	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



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